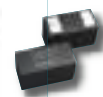


Our extensive package range provides maximum flexibility

	Miniaturization	>>	Medium Power
2 Pins	 DSN0402 (SOD992) 0.4 x 0.2 x 0.12  DSN0603-2 (SOD962) 0.6 x 0.3 x 0.3  DSN1006-2 (SOD993) 1.0 x 0.6 x 0.3  DSN1006U-2 (SOD995) 1.0 x 0.6 x 0.3  DFN1006D-2 (SOD882D) 1.0 x 0.6 x 0.37  DFN1006-2 (SOD882) 1.0 x 0.6 x 0.48  SOD523 1.2 x 0.8 x 0.6  DFN1608D-2 (SOD1608) 1.6 x 0.8 x 0.37  DSN1608-2 (SOD963/SOD964) 1.6 x 0.8 x 0.25/0.29  SOD323F 1.7 x 1.25 x 0.7  SOD323 1.7 x 1.25 x 0.95  SOD123F 2.6 x 1.6 x 1.1  CFP3 (SOD123W) 2.6 x 1.7 x 1.0  CFP5 (SOD128) 3.8 x 2.6 x 1.0  CFP15 (SOT1289) 5.8 x 4.3 x 0.78  D2PAK (SOT404) 11.0 x 10.0 x 4.3	 DFN1006B-3 (SOT883B) 1.0 x 0.6 x 0.37  DFN1006-3 (SOT883) 1.0 x 0.6 x 0.48	

Discretes semiconductors selection guide 2016

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Our commitment: quality and reliability

AEC-Q101

► We qualify our products according to the automotive AEC-Q101 standard and even exceed it's requirements, for instance when doing extended lifetime testing.



► All our processes and manufacturing plants are subject to regular international and internal audits, including the following:

- ISO9001
- ISO/TS 16949 for automotive sites
- ISO14001
- OHSAS18001



► NXP's Design for Excellence (DfX) program ensures that each new development builds on past learning and that best practices are always employed. The result is continual product improvement.



► Zero defect is our goal. To ensure continuous improvement failure analysis and the determination to find root causes is performed at all stages of development and production by adoption of quality-analysis tools and methods (e.g. Six-Sigma, Safe-Launch).

Rigorous attention to detail and commitment to quality have yielded a very low product failure rate of a single-digit part per billion (ppb).



Bipolar transistors

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High-power transistors up to 3 W

High-power transistors (single)

Package											LFPAK56 (SOT669)	
Size (mm)												
Size (mm)											5 × 6 × 1.1	
V _{CEO} (V)	I _C (A)	I _{CM} (A)	h _{FE} min/typ	@ I _C (A)	@ V _{CE} (V)	V _{CEsat} typ (mV); I _C = 0.5 A; I _B = 0.05 A	V _{CEsat} max (mV)	@ I _C (A)	@ I _B (A)	Polarity		
60	3	8	200 / 400	0.5	2	50	270	3	0.3	NPN	PHPT60603NY	
			200 / 400	0.5	2	70	360	3	0.3	PNP	PHPT60603PY	
100	3		150 / 250	0.5	10	50	330	3	0.3	NPN	PHPT61003NY	
			150 / 220	0.5	10	70	360	2	0.2	PNP	PHPT61003PY	
	2	6	150 / 250	0.5	10	50	300	2	0.2	NPN	PHPT61002NYC	
			150 / 220	0.5	10	70	400	2	0.2	PNP	PHPT61002PYC	

High-current, high

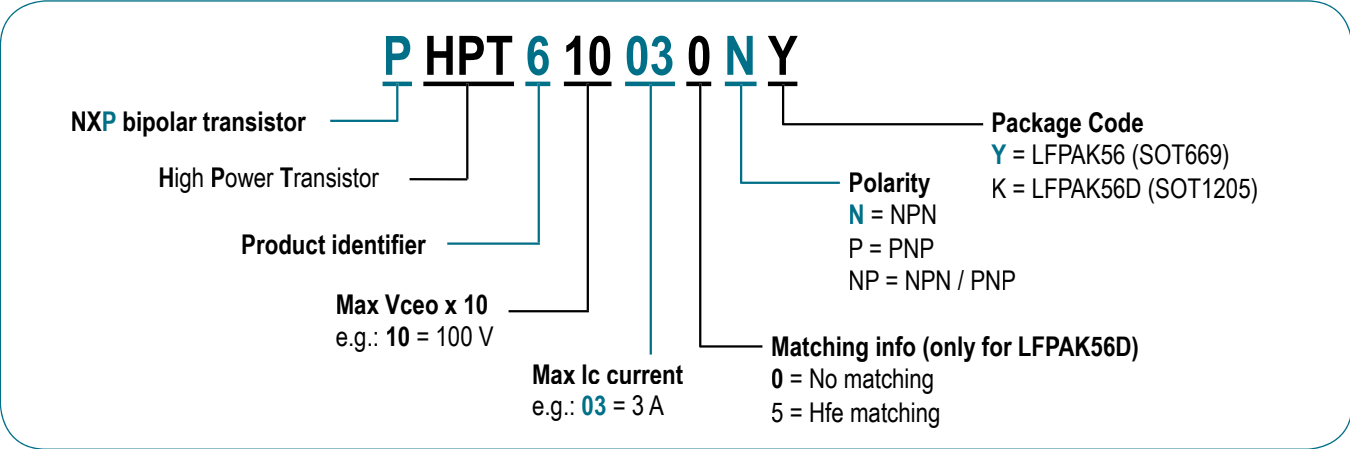
Low V_{CEsat} transistors up to 2000 mW

Low V_{CEsat} (BISS) transistors single PNP

types in **bold** represent new products

Package							SOT223 (SC-73)	SOT89 (SC-62)	SOT457 (SC-74)	DFN2020-3 (SOT1061)	DFN2020D-3 (SOT1061D)
Size (mm)							6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.5 x 1.0	2.0 x 2.0 x 0.62	2.0 x 2.0 x 0.62
P_{tot} (mW)							1700	1650	750	1300	1300
V_{CEO} (V)	I_C (A)	I_{CM} (A)	h_{FE} min/typ	@ I_C (A)	@ V_{CE} (V)	V_{CEsat} typ (mV); $I_C = 0.5$ A; $I_B = 0.05$ A					
12	5.3	10.6	250 / 400	0.5	2	20		PBSS301PX			
	5.7	11.4	250 / 400	0.5	2	20	PBSS301PZ				
	6	7	220 / 335	0.5	2	20			PBSS5612PA		
20	3	5	200 / –	0.5	2	80 ²⁾			PBSS5320D		
			220 / 450	0.5	2	50		PBSS5320X			
	4	15	250 / 400	0.5	2	35			PBSS301PD		
	5	10	300 / 430	0.5	2	45					

Nomenclature for high-power transistors



Low V_{CEsat} (BISS) transistors single NPN

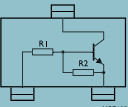
Package							SOT23	SOT323 (SC-70)	SOT363 (SC-88)	DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)	DFN1010D-3 (SOT1215)
Size (mm)							2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37	1.1 x 1.0 x 0.37
P_{tot} (mW)							480	350	430	250	250	750
V_{CE0} (V)	I_C (A)	I_{CM} (A)	h_{FE} min/typ	@ I_C (A)	@ V_{CE} (V)	V_{CEsat} typ (mV); $I_C = 0.5$ A; $I_B = 0.05$ A						
15	0.5	1	200 / 325	0.01	2	-				PBSS2515M	PBSS2515MB	
20	1	3	350 / 470	0.1	2	110 ²⁾	PBSS4120T					
	2											

High-voltage low V_{CEsat} (BISS) transistors

types in **bold** represent new products

Package			SOT223 (SC-73)	SOT89 (SC-62)	SOT1215	SOT23
Size (mm)			6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5		2.9 x 1.3 x 1.0
P _{tot} (mW)			1700	1300	750	250
Polarity	V _{CEO} (V)	I _C (A)				
NPN	150	0.5			PBHV8115QA	
		1	PBHV8115Z	PBHV8115X		PBHV8115T
		2	PBHV8215Z			
	180	1				PBHV8118T
	400	0.5	PBHV8540Z	PBHV8540X		PBHV8540T
		1	PBHV8140Z			
PNP	500	0.15				PMBTA45
	600	0.5	PBHV8560Z			
	140	4	PBHV9414Z			
	150	0.5			PBHV9115QA	
		1	PBHV9115Z	PBHV9115X		PBHV9115T
		2	PBHV9215Z			
	600	0.5	PBHV9560Z			
		0.1	PBHV3160Z			
	400	0.25	PBHV9040Z	PBHV9040X		

RETs 100 mA single - Part 1

Package					SOT23		SOT323 (SC-70)	
								
Size (mm)					2.9 x 1.3 x 1.0		2.0 x 1.25 x 0.95	
P _{tot} (mW)					250		200	
V _{CEO} (V)	I _C (mA)	Configuration	R1 (kΩ)	R2 (kΩ)	NPN		PNP	
50	100		1	1			PDTA113ET	PDTA113EU
			2.2	2.2	PDTC123ET		PDTA123ET	PDTA123EU
			4.7	4.7	PDTC143ET		PDTA143ET	PDTA143EU
			10	10	PDTC114ET		PDTA114ET	PDTA114EU
			22	22	PDTC124ET		PDTA124ET	PDTA124EU
			47	47	PDTC144ET		PDTA144ET	PDTA144EU
			100	100	PDTC115ET		PDTA115ET	PDTA115EU
			1	10				

Single transistors NPN

types in **bold** represent new products

Package						SOT23	SOT323 (SC-70)	DFN1010D-3 (SOT1215)	DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)
										
Size (mm)						2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	1.1 x 1.0 x 0.37	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37
P _{tot} (mW)						250	200	750	250	250
V _{CEO} (V)	I _C (mA)	h _{FE} min/typ	h _{FE} max	f _T min (MHz)						
25	100	450	1200	100			PMST5089			
30	100	110 - 200	450 - 800	100		BC848B	BC848W			
		350	900	100			PMST5088			
32	100	110 - 420	220 - 800	100		BCW31 / 32 / 33				
		180 - 380	310 - 630	250		BCW60B / C / D				
45	100	11								

Medium-power general-purpose transistors

Package						SOT223 (SC-73)	SOT89 (SC-62)	DFN2020-3 (SOT1061)	DFN2020D-3 (SOT1061D)
Size (mm)						6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.0 x 2.0 x 0.62	2.0 x 2.0 x 0.62
P _{tot} (mW)						1700	1300	1300	1300
Polarity	V _{CEO} (V)	I _C (A)	h _{FE} min	h _{FE} max	f _T min (MHz)				
NPN	20	2	85 - 160	375	40	BCP68 / -25	BC868 / -25	BC68PA / BC68-25PA	BC68PAS / BC68-25PAS
	45	1	63 - 100	160 - 250	100	BCP54 / -10 / -16	BCX54 / -10 / -16	BC54PA / BC54-10PA / BC54-16PA	BC54PAS / BC54-10PAS / BC54-16PAS
	60	1	63 - 100	160 - 250	100	BCP55 / -10 / -16	BCX55 / -10 / -16	BC55PA / BC55-10PA / BC55-16PA	BC55PAS / BC55-10PAS / BC55-16PAS
			100	300	100	BSP41	BSR41		
	80	1	63 - 100	160 - 250	100	BCP56 / -10 / -16	BCX56 / -10 / -16	BC56PA / BC56-10PA / BC56-16PA	BC56PAS / BC56-10PAS / BC56-16PAS

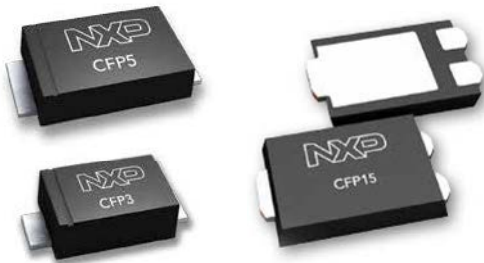
Darlington transistors

Package					SOT223 (SC-73)	SOT89 (SC-62)	SOT23
Size (mm)					6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.3 x 1.0
P _{tot} (mW)					1700	1300	250
Polarity	V _{CEO} (V)	I _C (mA)	h _{FE} min	f _T min (MHz)			
NPN	30	500	10000	125			PMBTA13
			20000		PZTA14	PXTA14	PMBTA14
						BCV29	BCV27
	45	1000	2000	200	BSP50	BST50	
			10000			BCV49	BCV47
	60	500	2000	200	BSP51	BST51	
PNP	30	500	20000	125			PMBTA64
			2000			BCV28	BCV26
			10000		BSP60	BST60	
	45	1000	2000	200		BCV48	BCV46
			10000		BSP61	BST61	
	60	500	2000	200	BSP62	BST62	

NXP's FlatPower packages
CFP3, CFP5, and CFP15

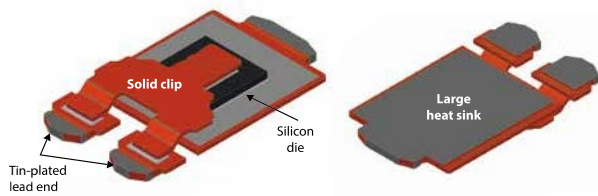
The medium-power solution for shrinking designs

Small SMD FlatPower packages
in three different versions



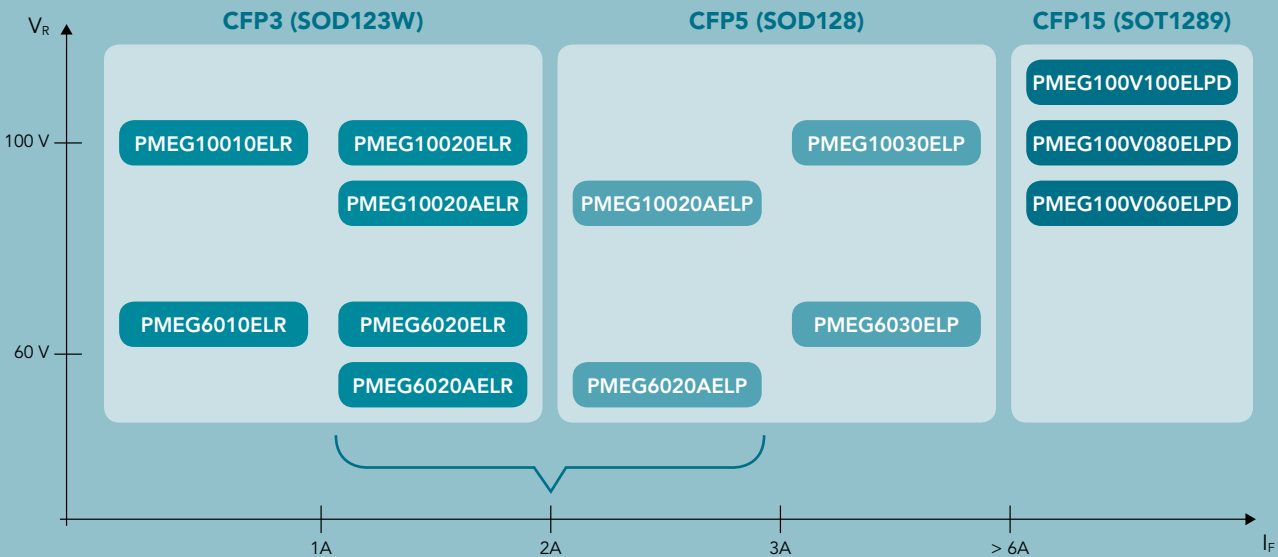
- Flat geometry, of down to 0.78 mm height
- Halogen-free mold compound
- AEC-Q101 qualified

Robust design



- High-power capability due to wire-free clip-bond technology and heatsink
- Automatic optical inspection of solder joint due to tin-plated lead ends
- Benchmark flat design of only 0.7 mm height

Low I_R Schottky Portfolio, AEC-Q101



NXP offers more than 200 products in FlatPower packages, to support a wide range of applications for medium-power rectification and surge protection.

Schottky barrier diodes and rectifiers

Medium-power low V_F Schottky rectifiers single ≥ 1 A - FlatPower packages

types in **bold**
represent
new products

I _F max (A)	V _R max (V)	V _F max (mV) @ I _F max
------------------------	------------------------	---

Controlled-avalanche switching diodes

V_R max (V)	V_F max (V)	@ I_F (mA)	I_R max (nA) @ V_R max	I_{FSM} max (A)	I_{FRM} max (mA)	C_d max (pF)	t_r max (ns)	Package	SOT23	SOT143B
								Size (mm)		
								P_{tot} (mW)	250	250
60	1	200	100	9	600	2.5	6			BAS56
90	1	200	100	10	600	35	50		BAS29	
									BAS31	
									BAS35	

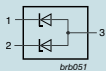
Low-leakage current-switching diodes

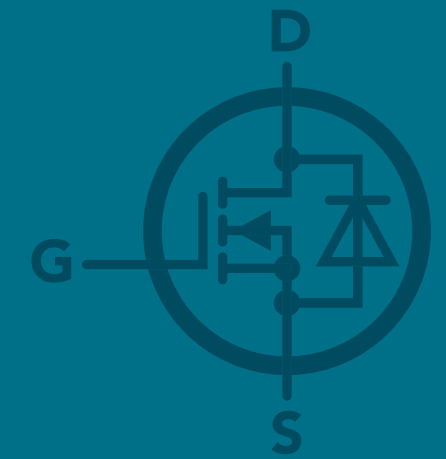
types in **bold** represent new products

V_R max (V)	V_F max (V)	@ I_F (mA)	I_R max (nA) @ V_R max	t_r max (μs)	Package	SOD80C
---------------	---------------	--------------	-------------------------------	----------------	---------	--------

Ultra low-capacitance ESD protection devices – Part 2

types in **bold** represent new products

Number of protected lines		V _{RWM} (V)	C _{line typ} (pF)	C _{line max} (pF)	ESD rating ^[1] max (kV)	Configuration	Type	Package	Size (mm)	
Unidirectional	Bidirectional									
2	1	5	0.5	0.65	10		PESD5V0X2UMB	DFN1006B-3 (SOT883B)	1.0 x 0.6 x 0.37	
							PESD5V0X2UM	DFN1006-3 (SOT883)	1.0 x 0.6 x 0.48	
							PESD5V0X2UAMB	DFN1006B-3 (SOT883B)	1.0 x 0.6 x 0.37	
			0.8	0.95	15		PESD5V0X2UAM	DFN1006-3 (SOT883)	1.0 x 0.6 x 0.48	
							PESD5V0X1BQ	SOT663	1.6 x 1.2 x 0.55	
							PESD5V0X1BT	SOT23	2.9 x 1.3 x 1.0	
	0	5.5	1	1.5	8					



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